

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Darrel R. Bloomquist et al.	Examiner:	Tuan T. Nguyen
Serial No.:	10/080,847	Group Art Unit:	2824
Filed:	Feb. 2, 2002	Docket No.:	10013884-1
Title:	IN-PLANE TOROIDAL MEMORY CELL WITH VERTICALLY STEPPED CONDUCTOR		

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Mail Stop: Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please enter the following Response to Examiner's Reasons for Allowance.
Remarks begin on page 2.

AUTHORIZATION TO DEBIT ACCOUNT

It is believed that no extensions of time or fees for net addition of claims are required, beyond those, which may otherwise be provided for in documents accompanying this paper. However, in the event that additional extensions of time are necessary to allow consideration of this paper, such extensions are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefore (including fees for net addition of claims) are hereby authorized to be charged to Hewlett-Packard Development Company's deposit account no. 08-2025.

**Comments on Statement for Reasons for Allowance**

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Title: IN-PLANE TOROIDAL MEMORY CELL WITH VERTICALLY STEPPED CONDUCTOR**REMARKS**

The Examiner's provides the following reasons for allowance for claims 1-7, 9-10 and 12-16:

"The prior art of record fails to disclose a write conductor layout for a magnetic random access memory device, in combination with other cited limitations, wherein the first and second conductors each have a stepped portion which is aligned with the first axis as they pass through the axial opening of the memory cell as recited in claims 1-7.

The prior art of record further fails to disclose a magnetic random access memory device, in combination with other cited limitations, wherein an electrical current applied to each of a pair of the conductors creates a first magnetic field and a second magnetic field in one of the memory cells that intersects the pair of conductors and creates either the first magnetic field or the second magnetic field in the magnetic memory cells that do not intersect the pair of conductors as recited in claims 9-10 and 12-16."

Applicant agrees that claims 1-7, 9-10, and 12-16 are allowable for at least these reasons. However, the claims are allowable for other reasons as well. Applicant submits that the present claims are allowable for at least the reason that the references of record in the application do not teach or suggest all the limitations of the claims as recited in the claims themselves.

Date: March 25, 05

Respectfully submitted,

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